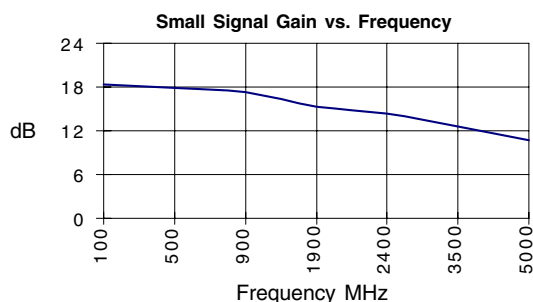


Product Description

Stanford Microdevices' SGA-3486 is a high performance cascadeable 50-ohm amplifier designed for operation at voltages as low as 2.9V. This RFIC uses the latest Silicon Germanium Heterostructure Bipolar Transistor (SiGe HBT) process featuring 1 micron emitters with F_T up to 65 GHz.

This circuit uses a darlington pair topology with resistive feedback for broadband performance as well as stability over its entire temperature range. Internally matched to 50 ohm impedance, the SGA-3486 requires only DC blocking and bypass capacitors for external components.



Preliminary

SGA-3486

DC-2000 MHz Silicon Germanium Cascadeable Gain Block



Product Features

- DC-2000 MHz Operation
- Single Voltage Supply
- High Output Intercept: +24.6dBm typ. at 850 MHz
- Low Current Draw: 35mA at 2.9V typ.
- Low Noise Figure: 2.8dB typ. at 850 MHz

Applications

- Oscillator Amplifiers
- PA for Low Power Applications
- IF/RF Buffer Amplifier
- Drivers for CATV Amplifiers

Symbol	Parameters: Test Conditions: $Z_0 = 50 \text{ Ohms}$, $I_d = 35 \text{ mA}$, $T = 25^\circ\text{C}$		Units	Min.	Typ.	Max.
P_{1dB}	Output Power at 1dB Compression	$f = 850 \text{ MHz}$ $f = 1950 \text{ MHz}$	dBm dBm		12.7 12.5	
S_{21}	Small Signal Gain	$f = \text{DC} - 1000 \text{ MHz}$ $f = 1000 - 2000 \text{ MHz}$	dB dB	19.0	21.2 18.0	
S_{12}	Reverse Isolation	$f = \text{DC} - 2000 \text{ MHz}$	dB		23.1	
S_{11}	Input VSWR	$f = \text{DC} - 2000 \text{ MHz}$	-		1.67:1	
S_{22}	Output VSWR	$f = \text{DC} - 2000 \text{ MHz}$	-		1.33:1	
IP_3	Third Order Intercept Point	$f = 850 \text{ MHz}$ $f = 1950 \text{ MHz}$	dBm dBm		24.6 26.9	
NF	Noise Figure	$f = \text{DC} - 1000 \text{ MHz}$ $f = 1000 - 2000 \text{ MHz}$	dB dB		2.8 3.4	
T_D	Group Delay	$f = 1000 \text{ MHz}$	pS		119.0	
V_D	Device Voltage		V	2.6	2.9	3.2

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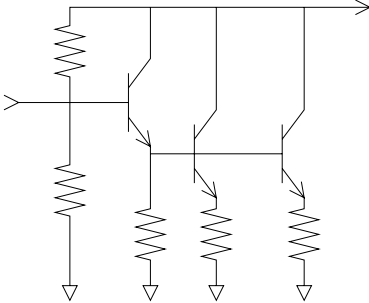
522 Almanor Ave., Sunnyvale, CA 94086

Phone: (800) SMI-MMIC

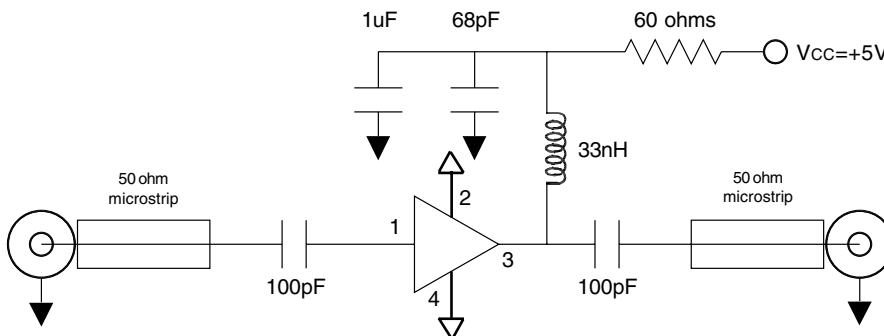
<http://www.stanfordmicro.com>

EDS-100635 Rev A

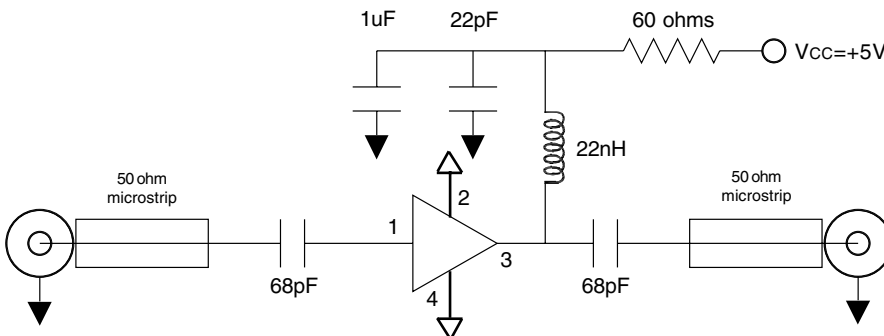
Parameter	Specification			Unit	Test Condition
	Min	Typ.	Max.		
Device Bias					T= 25C
Operating Voltage		2.9		V	
Operating Current		35.0		mA	
500 MHz					T= 25C
Gain		22.4		dB	
Noise Figure		2.8		dB	
Output IP3		25.4		dBm	
Output P1dB		12.3		dBm	
Input Return Loss		15.7		dB	
Isolation		24.8		dB	
850 MHz					T= 25C
Gain		21.2		dB	
Noise Figure		2.8		dB	
Output IP3		24.6		dBm	
Output P1dB		12.7		dBm	
Input Return Loss		12.9		dB	
Isolation		24.4		dB	
1950 MHz					T= 25C
Gain		18.0		dB	
Noise Figure		3.4		dB	
Output IP3		26.9		dBm	
Output P1dB		12.5		dBm	
Input Return Loss		12.0		dB	
Isolation		23.1		dB	
2400 MHz					T= 25C
Gain		16.5		dB	
Noise Figure		3.5		dB	
Output IP3		28.1		dBm	
Output P1dB		12.4		dBm	
Input Return Loss		10.8		dB	
Isolation		22.1		dB	

Pin #	Function	Description	Device Schematic
1	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.	
2	GND	Connection to ground. Use via holes for best performance to reduce lead inductance as close to ground leads as possible.	
3	RF OUT/BIAS	RF output and bias pin. DC voltage is present on this pin, therefore a DC blocking capacitor is necessary for proper operation.	
4	GND	Sames as Pin 2	

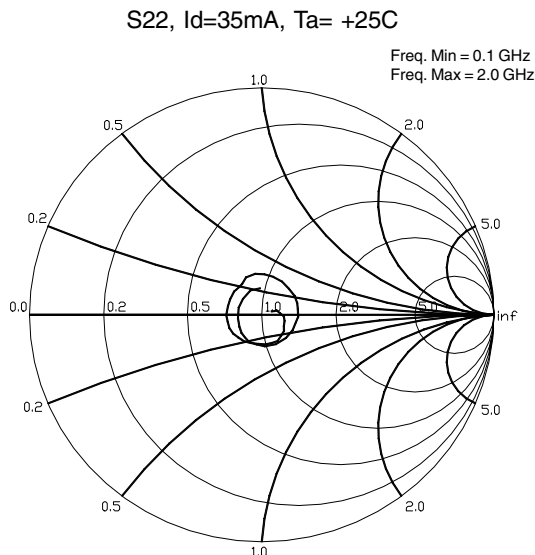
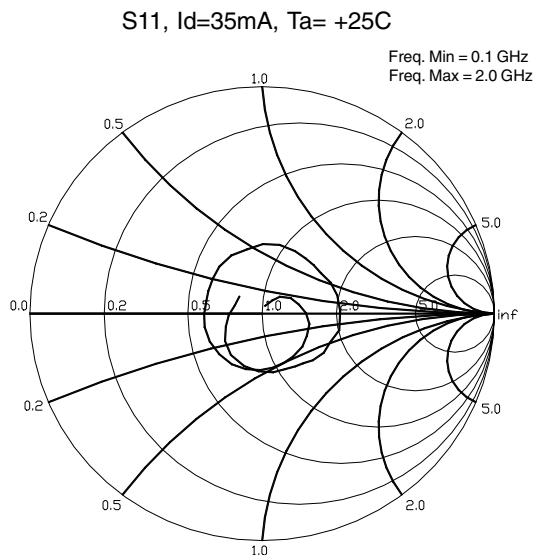
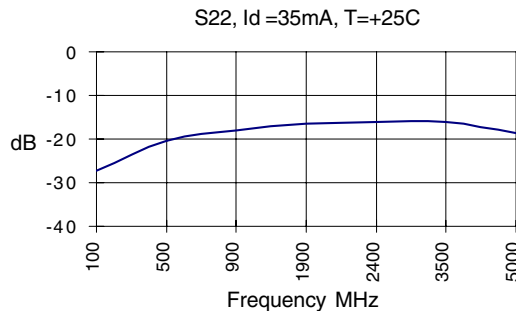
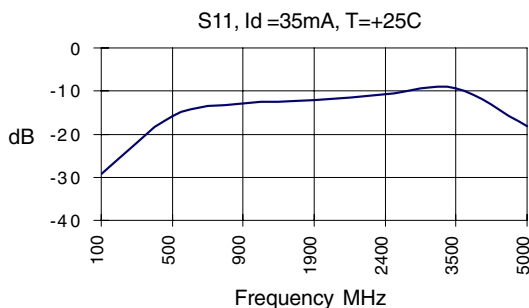
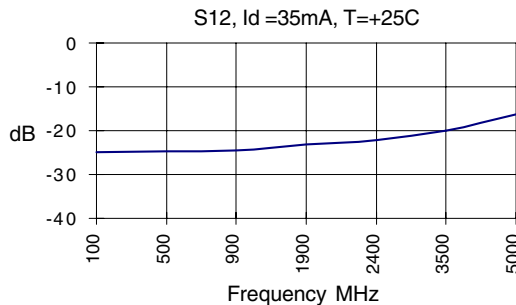
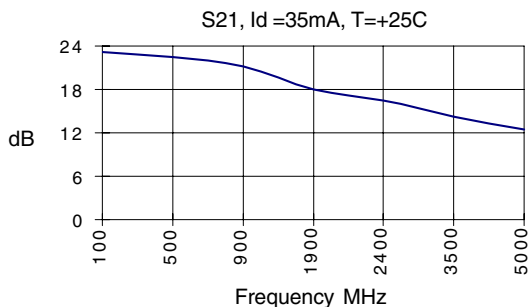
Application Schematic for +5V Operation at 900 MHz



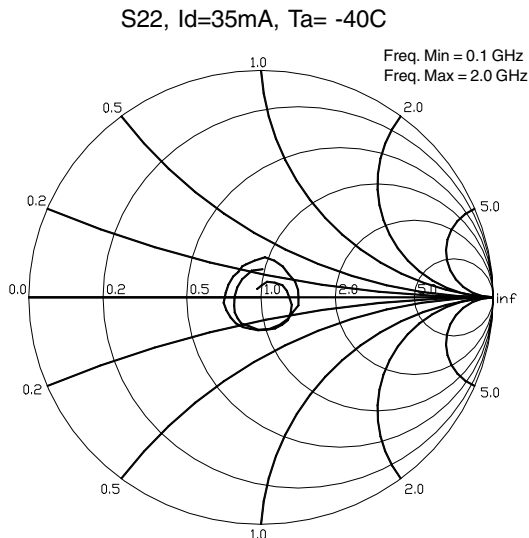
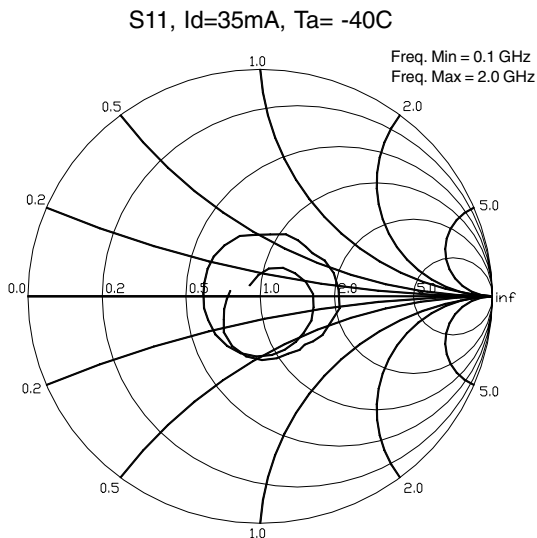
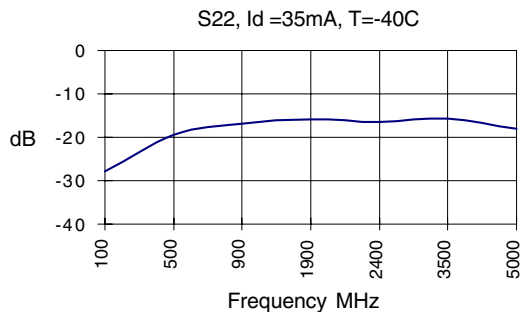
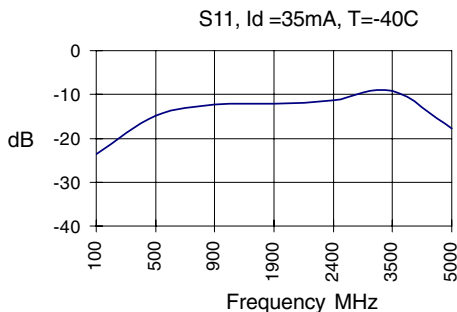
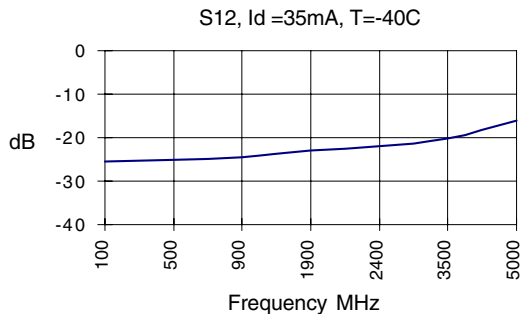
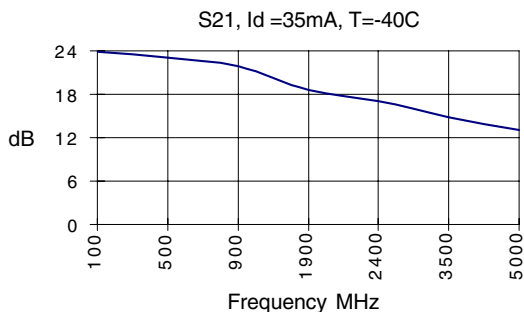
Application Schematic for +5V Operation at 1900 MHz



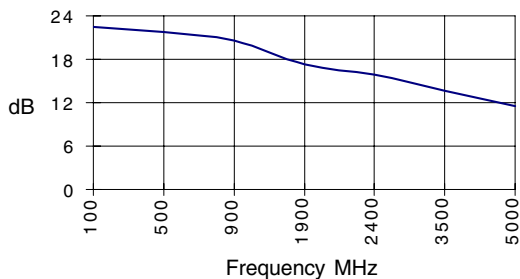
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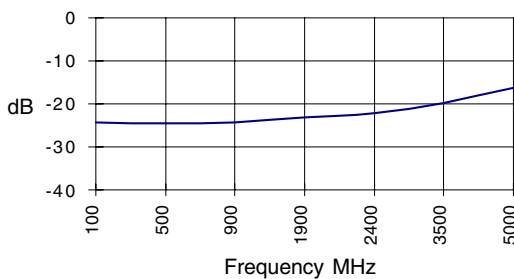
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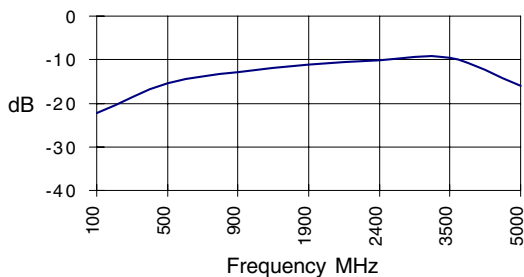
S21, Id =35mA, T=85C



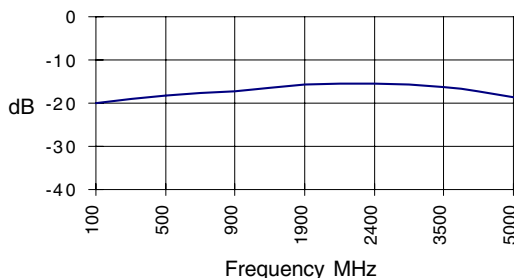
S12, Id =35mA, T=85C



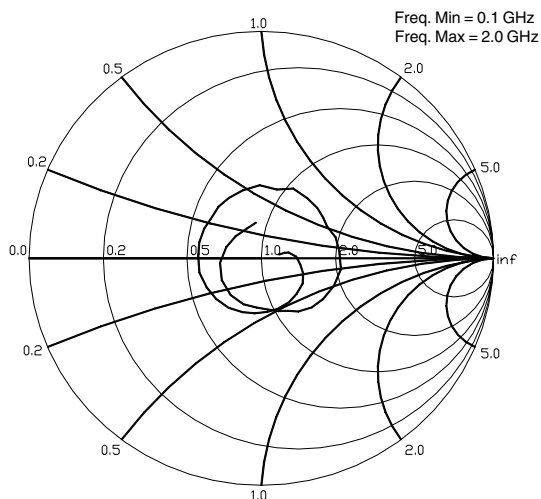
S11, Id =35mA, T=85C



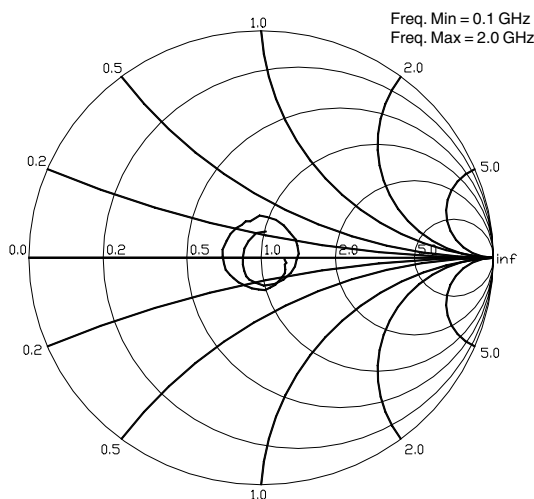
S22, Id =35mA, T=85C



S11, Id=35mA, Ta= 85C



S22, Id=35mA, Ta= 85C



Absolute Maximum Ratings

Parameter	Value	Unit
Supply Current	70	mA
Operating Temperature	-40 to +85	C
Maximum Input Power	+16	dBm
Storage Temperature Range	-40 to +85	C
Operating Junction Temperature	+150	C

Caution:



Operation of this device above any one of these parameters may cause permanent damage. Appropriate precautions in handling, packaging and testing devices must be observed.

Thermal Resistance (Lead-Junction):
97° C/W

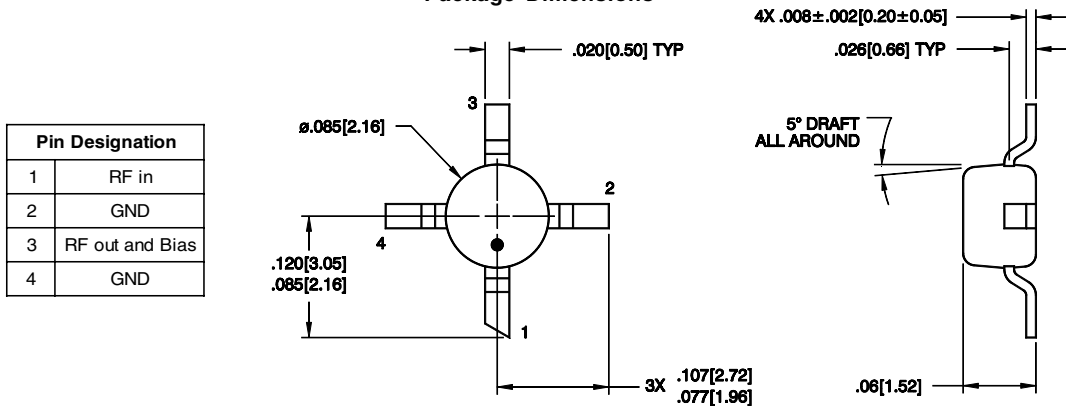
Part Number Ordering Information

Part Number	Reel Size	Devices/Reel
SGA-3486-TR1	7"	1000
SGA-3486-TR2	13"	3000

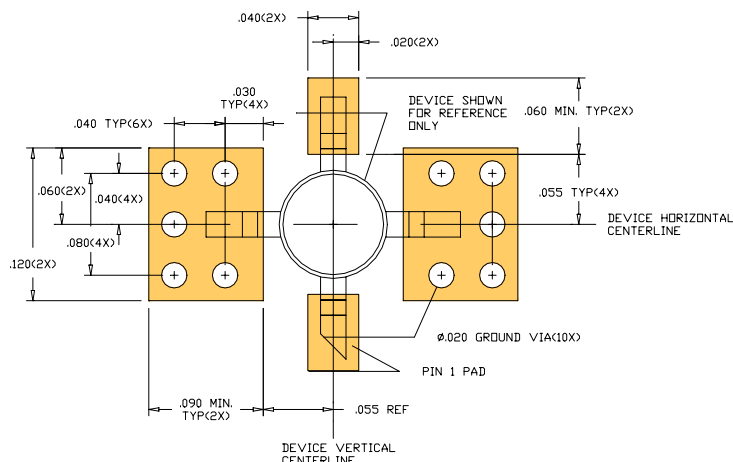
Recommended Bias Resistor Values

Supply Voltage(Vs)	4V	5V	7.5V	9V	12V
Rbias (Ohms)	18	40	96	129	196

Package Dimensions



PCB Pad Layout



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